## **HAMAMATSU**

# MCP ASSEMBLY **F2223-21SH**

This MCP assembly is a suitable detector for an electron or ion beam in SEM, SIM or Lithography.

It is possible to detect some signal from a sample with high sensitivity, that can be performed with the compactness and the center hole of this assembly. It allows to set this assembly at close position to the sample and gives better efficiency in the beam detection.



TMCPF0020

#### **FEATURES**

- High Sensitivity
- ●High S/N Ratio
- **●Wide Dynamic Range**
- **●**Center Hole for Beam Line
- Compact and Lightweight

#### **APPLICATIONS**

- Scanning Electron Microscopy
- Scanning Ion Microscopy
- ●Electron Lithography
- •Mask Aligner
- ●Electron Beam Measuring System
- ●lon Scattering Spectroscopy

#### **SPECIFICATIONS**

#### **GENERAL**

| Parameter            | Value | Unit |
|----------------------|-------|------|
| Assembly Outer Size  | φ56.5 | mm   |
| Effective Area       | φ27.0 | mm   |
| Height (Max.)        | 8.6   | mm   |
| MCP Channel Diameter | 12    | μm   |
| Number of MCPs       | 2     | _    |
| MCP Center Dead Area | φ8    | mm   |

#### **RATINGS**

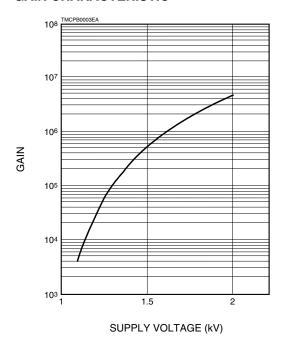
| MCP Supply Voltage (Max.)              | 2                      | kV    |
|--|------------------------|-------|
| MCP-Out to Anode Supply Voltage (Max.) | 0.5                    | kV    |
| Mesh to MCP-In Supply Voltage          | 0.5                    | kV    |
| Anode to Substrate Supply Voltage      | 3                      | kV    |
| Operating Vacuum Condition (Max.)      | 1.3 × 10 <sup>-4</sup> | Pa    |
| Ambient Temperature                    | +10 to +40             | °C    |
| Baking Temperature                     | 300                    | °C    |
| Baking Time                            | 10                     | Hours |
| Vacuum Condition for Baking (Max.)     | 1.3 × 10 <sup>-4</sup> | Pa    |

#### TYPICAL ELECTRICAL CHARACTERISTICS (Supply Voltage: 2 kV, Vacuum: 1.3 × 10<sup>-4</sup> Pa, Operating Ambient Temperature: +25 °C)

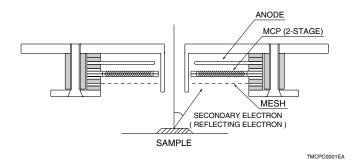
| Gain at 1.8 kV (Min.) | $1 \times 10^6$  | _                   |
|-----------------------|--|---------------------|
| Plate Resistance      | 20 to 40   | $M\Omega$ / $MCP$   |
| Maximum Linear Output | 7 % of strip current under uniform input into whole MCP effective area | _                   |
| Dark Current          | 20   | pA⋅cm <sup>-2</sup> |

Subject to local technical requirements and regulations, availability of products included in this promotional material may vary. Please consult with our sales office. Information furnished by HAMAMATSU is believed to be reliable. However, no responsibility is assumed for possible inaccuracies or omissions. Specifications are subject to change without notice. No patent rights are granted to any of the circuits described herein. ©2006 Hamamatsu Photonics K.K.

#### **GAIN CHARACTERISTIC**



#### **CONSTRUCTION AND APPLICATION EXAMPLE**

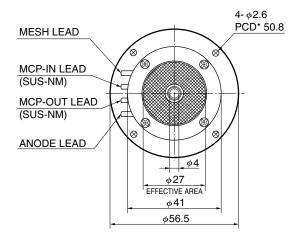


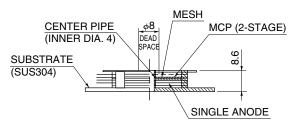
#### **WIRING POTENTIAL EXAMPLE**

| MESH                   | +200 V   |
|------------------------|----------|
| MCP-IN                 | +500 V   |
| MCP-OUT                | +2300 V  |
| ANODE                  | +2400 V  |
| CENTER PIPE AND SUBSTF | RATE GND |
| SAMPLE                 | GND      |

<sup>\*</sup> This is an example potential to detect secondary electrons. For other applications, please consult to our sales office.

#### **DIMENSIONAL OUTLINES (Unit: mm)**





\* PCD (Pitch Circle Diameter)

TMCPA0002EE

### HAMAMATSU

WEB SITE www.hamamatsu.com

HAMAMATSU PHOTONICS K.K., Electron Tube Division

314-5, Shimokanzo, Iwata City, Shizuoka Pref., 438-0193, Japan, Telephone: (81)539/62-5248, Fax: (81)539/62-2205